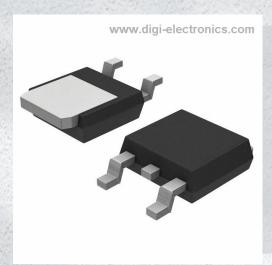


MJD350T4 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number MJD350T4-DG

Manufacturer onsemi

Manufacturer Product Number MJD350T4

Description TRANS PWR PNP 0.5A 300V DPAK

Detailed Description Bipolar (BJT) Transistor PNP 300 V 500 mA 15 W Sur

face Mount DPAK



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MJD350T4	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
PNP	500 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
300 V	
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100μΑ	30 @ 50mA, 10V
Power - Max:	Frequency - Transition:
15 W	
Operating Temperature:	Mounting Type:
-65°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-252-3, DPAK (2 Leads + Tab), SC-63	DPAK
Base Product Number:	
MJD35	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
RoHS non-compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	



High Voltage Power Transistors

DPAK for Surface Mount Applications

MJD340 (NPN), MJD350 (PNP)

Designed for line operated audio output amplifier, switchmode power supply drivers and other switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Electrically Similar to Popular MJE340 and MJE350
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

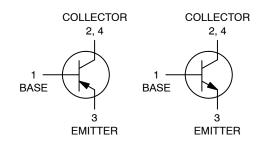
MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	300	Vdc
Collector-Base Voltage	V _{CB}	300	Vdc
Emitter-Base Voltage	V _{EB}	3	Vdc
Collector Current - Continuous	I _C	0.5	Adc
Collector Current - Peak	I _{CM}	0.75	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	15 0.12	W W/°C
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.56 0.012	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C
ESD - Human Body Model MJD340 (NPN) MJD350 (PNP)	НВМ	3B 2	V
ESD – Machine Model MJD340 (NPN) MJD350 (PNP)	ММ	M4 M4	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

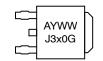
SILICON POWER TRANSISTORS 0.5 AMPERE 300 VOLTS, 15 WATTS





DPAK CASE 369C STYLE 1

MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week J3x0 = Device Code

x= 4 or 5 G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

These ratings are applicable when surface mounted on the minimum pad sizes recommended.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	8.33	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	80	°C/W
Leading Temperature for Soldering Purpose	TL	260	°C

^{2.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (Note 3) (I _C = 1 mA, I _B = 0)	V _{CEO(sus)}	300	-	V
Collector Cutoff Current (V _{CB} = 300 V, I _E = 0)	I _{CEO}	-	0.1	mA
Emitter Cutoff Current (V _{BE} = 3 V, I _C = 0)	I _{EBO}	-	0.1	mA
ON CHARACTERISTICS (Note 3)				
DC Current Gain (I _C = 50 mA, V _{CE} = 10 V)	h _{FE}	30	240	_
Collector–Emitter Saturation Voltage (I _C = 100 mA, I _B = 10 mA)	V _{CE(sat)}	-	1	V
Base-Emitter On Voltage (I _C = 1 A, V _{CE} = 10 V)	V _{BE(on)}	-	1.5	V
DYNAMIC CHARACTERISTICS				
Current Gain – Bandwidth Product (I _C = 50 mA, V _{CE} = 10 V, f = 10 MHz)	f _T	10	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS

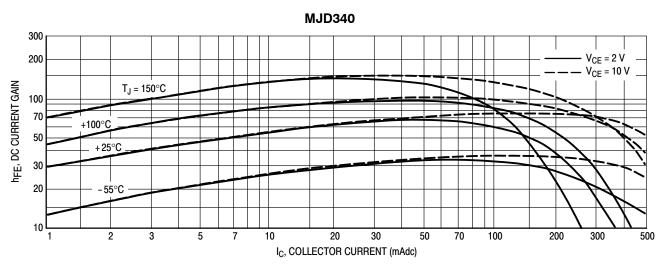


Figure 1. DC Current Gain

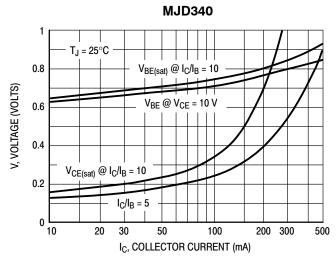
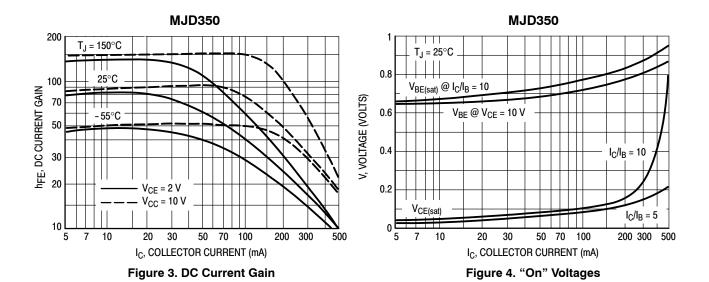


Figure 2. "On" Voltages



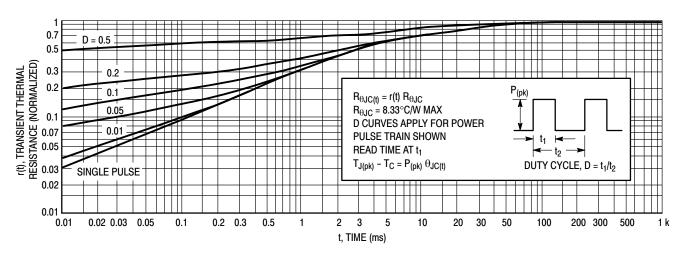


Figure 5. Thermal Response

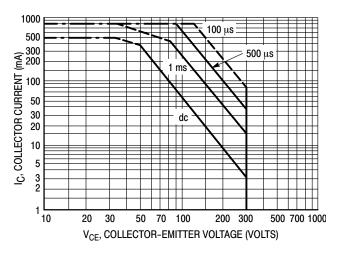


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_{J(pk)} = 150^{\circ} C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ} C$. $T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

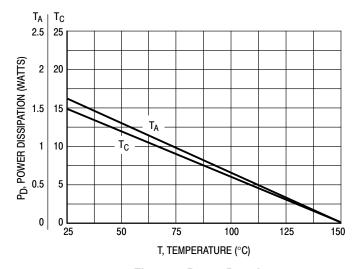


Figure 7. Power Derating

ORDERING INFORMATION

Device	Package	Shipping [†]	
MJD340G	DPAK (Pb-Free)	75 Units / Rail	
MJD340RLG	DPAK (Pb-Free)	1,800 / Tape & Reel	
MJD340T4G	DPAK (Pb-Free)	2,500 / Tape & Reel	
MJD340T4GN	DPAK (Pb-Free)	2,500 / Tape & Reel	
NJVMJD340T4G	DPAK (Pb-Free)	2,500 / Tape & Reel	
MJD350G	DPAK (Pb-Free)	75 Units / Rail	
MJD350T4G	DPAK (Pb-Free)	2,500 / Tape & Reel	
MJD350T4GN	DPAK (Pb-Free)	2,500 / Tape & Reel	
NJVMJD350T4G	DPAK (Pb-Free)	2,500 / Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

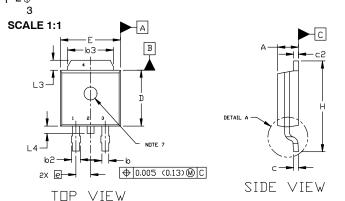


MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE) CASE 369C **ISSUE G**

DATE 31 MAY 2023



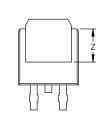


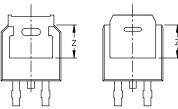
- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS 63, L3. AND Z.
- L3, AND Z.

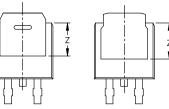
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR
 GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
 DIMENSIONS D AND E ARE DETERMINED AT THE
 OUTERMOST EXTREMES OF THE PLASTIC BODY.
 DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
 DETININAL MOLD ESCALUPE.

- OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
ויונע	MIN.	MAX.	MIN.	MAX.
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090 BSC		2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90	REF
L2	0.020 BSC		0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	







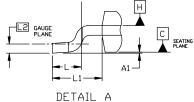
BOTTOM VIEW

BOTTOM VIEW AL TERNATE CONSTRUCTIONS

5.80 [0.228] 6.20 [0.244] 2.58 3.00 [0.102] [0.118] 1.60 [0.063] 6.17 [0.243]

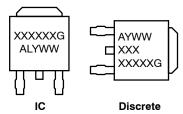
RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DUWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.



CW ROTATED 90°

GENERIC MARKING DIAGRAM*



XXXXXX	= Device Code
Α	= Assembly Location
L	= Wafer Lot
Υ	= Year
WW	= Work Week
G	= Pb-Free Package

STYLE 1: PIN 1. BASE STYLE 2: PIN 1. GATE STYLE 3: PIN 1. ANODE STYLE 4: PIN 1. CATHODE

STYLE 5: PIN 1. GATE 2. COLLECTOR 2. DRAIN 2. CATHODE 2. ANODE 2. ANODE 3 SOURCE 3 CATHODE 3 FMITTER 3 ANODE 3 GATE COLLECTOR 4. DRAIN CATHODE 4. ANODE ANODE

STYLE 6: STYLE 7: PIN 1. GATE 2. COLLECTOR STYLE 8: STYLE 9: STYLE 10: PIN 1. MT1 2. MT2 PIN 1. N/C 2. CATHODE 3. ANODE PIN 1. ANODE 2. CATHODE PIN 1. CATHODE 2. ANODE 3 CATHODE 3 FMITTER 3 RESISTOR ADJUST 3 GATE 4. MT2 4. COLLECTOR 4. CATHODE 4. ANODE CATHODE

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON10527D	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

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ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales



OUR CERTIFICATE

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